

L Number	Hits	Search Text	DB	Time stamp
-	1778	349/139	USPAT; US-PGPUB; JPO	2003/09/02 15:16
-	1121	349/138	USPAT; US-PGPUB; JPO	2002/12/19 10:39
-	240	349/147	USPAT; US-PGPUB; JPO	2002/12/19 10:39
-	1194	349/149	USPAT; US-PGPUB; JPO	2002/12/19 10:39
-	284	349/151	USPAT; US-PGPUB; JPO	2002/12/19 10:39
-	1199	349/153	USPAT; US-PGPUB; JPO	2002/12/19 10:39
-	202	349/190	USPAT; US-PGPUB; JPO	2002/12/19 10:40
-	4624	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)	USPAT; US-PGPUB; JPO	2002/12/19 10:56
-	440	349/139 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	USPAT; US-PGPUB; JPO	2002/12/19 11:32
-	421	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and ((signal adj line) or drain or source or data) and corrosion	USPAT; US-PGPUB; JPO	2002/12/19 11:04
-	300	349/149 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	USPAT; US-PGPUB; JPO	2002/12/19 11:27
-	35	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and (signal adj line) and corrosion and gap	USPAT; US-PGPUB; JPO	2002/12/19 15:32
-	24	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and (signal adj line) and corrosion and gap and drive and terminal	USPAT; US-PGPUB; JPO	2002/12/19 15:41
-	172	349/153 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	USPAT; US-PGPUB; JPO	2002/12/20 11:08
-	57	349/139 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain) and corrosion	USPAT; US-PGPUB; JPO	2002/12/20 11:30
-	29	349/138 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain) and corrosion	USPAT; US-PGPUB; JPO	2002/12/20 11:49
-	4	349/190 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain) and corrosion	USPAT; US-PGPUB; JPO	2002/12/20 15:14
-	20	349/138 and (stack\$4 or laminat\$4 or multi\$5) and (signal adj line) and corrosion	USPAT; US-PGPUB; JPO	2002/12/20 15:17
-	50	349/149 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain) and corrosion	USPAT; US-PGPUB; JPO	2002/12/20 15:20
-	145	349/147 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	USPAT; US-PGPUB; JPO	2002/12/20 15:34
-	129	349/151 and (stack\$4 or laminat\$4 or multi\$5) and (signal or source or drain)	USPAT; US-PGPUB; JPO	2002/12/20 15:44

-	74	((stack\$4 or lamilat\$4 or multi\$5) with layer\$4) and (insulat\$4 same (semiconduct\$4 or silicon) same protect\$4)) and (signal adj line) and corrosion	USPAT; US-PGPUB; JPO	2002/12/20 16:06
-	42848	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4))	USPAT	2003/08/29 09:33
-	2884	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)	USPAT	2003/08/29 09:33
-	8367	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 10:07
-	96	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and 349/149	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 09:39
-	154	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and 349/139	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 09:59
-	3245	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and terminal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 10:08
-	1329	(driv\$4 or chip or semiconductor\$) and ((stack\$4 or laminat\$4) with (AS or semiconductor\$4)) and (liquid adj crystal)and terminal and peripheral	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 10:10
-	133	QI.xa.	USPAT	2003/08/29 10:37
-	431214	pcb (printed adj circuit) driv\$3 adj circuit	USPAT;	2003/09/02 15:22
-		IC (integrated adj circuit)	US-PGPUB	
-	352493	semiconductor	USPAT;	2003/09/02 15:21
-	817	(349/149-152).ccls.	USPAT; US-PGPUB	2003/09/02 15:21
-	284155	pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit) near10 periphery near10 semiconductor	USPAT; US-PGPUB	2003/09/02 15:24
-	9	(pcb or (printed adj circuit) or (driv\$3 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor and ((349/149-152).ccls.)	USPAT; US-PGPUB	2003/09/02 15:53
-	399	(pcb or (printed adj circuit) or (driv\$3 adj circuit IC) or (integrated adj circuit)) near10 periphery near10 semiconductor	USPAT; US-PGPUB	2003/09/02 15:47
-	399	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor	USPAT; US-PGPUB	2003/09/02 16:56
-	0	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor near10 ((stack or laminat\$4) with insulat\$4)	USPAT; US-PGPUB	2003/09/02 16:21
-	0	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor near10 ((stack or laminat\$4) near10 insulat\$4)	USPAT; US-PGPUB	2003/09/02 16:28
-	62	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor and ((stack or laminat\$4) near10 insulat\$4)	USPAT; US-PGPUB	2003/09/02 16:28
-	76	(pcb (printed adj circuit) driv\$3 adj circuit IC (integrated adj circuit)) near10 periphery near10 semiconductor and (liquid adj crystal)	USPAT; US-PGPUB	2003/09/02 16:57
-	1	6697139.pn.	USPAT	2004/05/12 15:25

-	1	5847781.pn.	USPAT	2004/05/13 13:37
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